

REMARKS

The Office Action of May 21, 2003 was received and reviewed. Applicants would like to thank the Examiner for the consideration given to the above-identified application.

By the foregoing amendment claims 5-12, 16, 19, 26-48, and 67-75 have been canceled and claims 85-120 have been newly added. Accordingly, claims 1-48 and 68-84 are canceled, claims 49-67 are withdrawn from consideration and claim 85-120 are currently pending in the application.

Referring now to the detailed Office Action, claims 5-12, 16, 19, 26-48, and 67-75 stand rejected under 35 U.S.C. §103(a) as unpatentable over Oka (JP '915 – hereinafter Oka) in combination with Liu et al. (U.S. '826 – hereinafter Liu), Kuznetsov (Inst. Phys. Conf. – hereinafter Kuznetsov), and Kumomi. Further, claims 9-10 stand rejected under 35 U.S.C. §103(a) as unpatentable over Oka in combination with Liu, Kuznetsov, Kumomi, and further in view of Yonehara (U.S. '093 – hereinafter Yonehara) and/or Shibata (U.S. '244 – hereinafter Shibata). Applicants respectfully submit that, by the foregoing amendment canceling claims 5-12, 16, 19, 26-48, and 67-75, these rejections have been rendered moot.

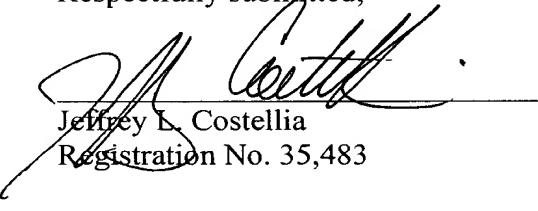
The newly added independent claims recite, for example as set forth in claim 85, a method for manufacturing a semiconductor device comprising the steps of forming a semiconductor film over a substrate, disposing a crystallizing promoting material in contact with a selected portion of the semiconductor film, crystallizing the semiconductor film by heating, patterning the crystalline semiconductor film to an active layer including the selected portion, forming a gate insulating film over the active layer, forming a gate electrode over the gate insulating film, forming an insulating film over the gate insulating film, and forming a wiring over the insulating film, wherein the wiring is connected to the selected portion. These claims should be considered acceptable in this application since they are generic to the prior election of species, in that the semiconductor film is formed over "a substrate."

Applicants respectfully contend that the none of the prior art documents employed in the rejection of the canceled claims teach or suggest the combination of features recited above. Specifically, Applicants believe that the prior art of record does not appear to disclose forming a wiring over the insulating film, wherein the wiring is connected to a selected portion to which a crystallizing promoting material has been disposed, as now variously recited in the independent claims.

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Thus, Applicants respectfully request consideration and allowance of the present application in view of the amendments provided above. It is submitted that claims 85-120 are now in condition for allowance. An early and favorable Notice of Allowance is respectfully solicited. In the event that the Examiner is of the opinion that a brief telephone or personal interview will facilitate allowance of one or more of the above claims, the Examiner is courteously requested to contact Applicant's undersigned representative.

Respectfully submitted,


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